## **20V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **SUMMARY**

 $V_{(BR)DSS} = 20V : R_{DS}(on) = 0.06\Omega; I_D = 4.1A$ 

#### **DESCRIPTION**

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



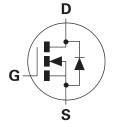
SOT23

#### **FEATURES**

- Low on-resistance
- Fast switching speed
- Low threshold
- · Low gate drive
- SOT23 package

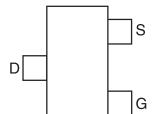
## **APPLICATIONS**

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control



#### **ORDERING INFORMATION**

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL	
ZXMN2A14FTA	7″	8mm	3000 units	



**PINOUT** 

## **DEVICE MARKING**

• 214



## **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current @ V <sub>GS</sub> =4.5V; T <sub>A</sub> =25°C <sup>(b)</sup>	I <sub>D</sub>	4.1	А
@ V <sub>GS</sub> =4.5V; T <sub>A</sub> =70°C (b)		3.3	Α
@ V <sub>GS</sub> =4.5V; T <sub>A</sub> =25°C <sup>(a)</sup>		3.4	А
Pulsed Drain Current (c)	I <sub>DM</sub>	19	А
Continuous Source Current (Body Diode) (b)	I <sub>S</sub>	1.7	А
Pulsed Source Current (Body Diode) (c)	I <sub>SM</sub>	19	А
Power Dissipation at T <sub>A</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	1	W
Linear Derating Factor		8	mW/°C
Power Dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	1.5	W
Linear Derating Factor		12	mW/°C
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

### THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient <sup>(a)</sup>	$R_{\Theta JA}$	125	°C/W
Junction to Ambient <sup>(b)</sup>	$R_{\Theta JA}$	82	°C/W

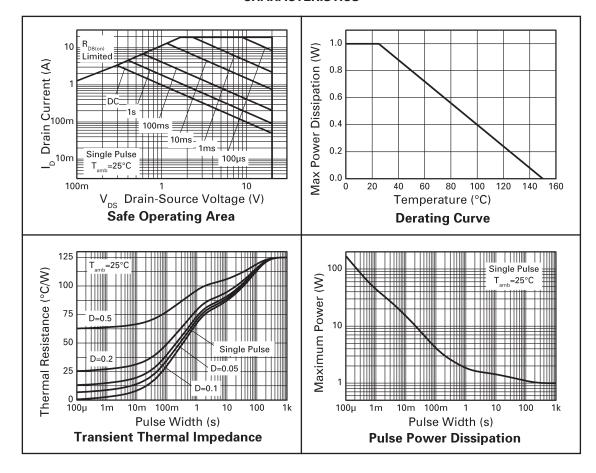
## NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.



 <sup>(</sup>b) For a device surface mounted on FR4 PCB measured at t ≤ 5 sec.
(c) Repetitive rating - 25mm x 25mm FR4 PCB, D=0.02, pulse width 300 μs - pulse width limited by maximum junction temperature.

#### **CHARACTERISTICS**





# **ELECTRICAL CHARACTERISTICS** (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

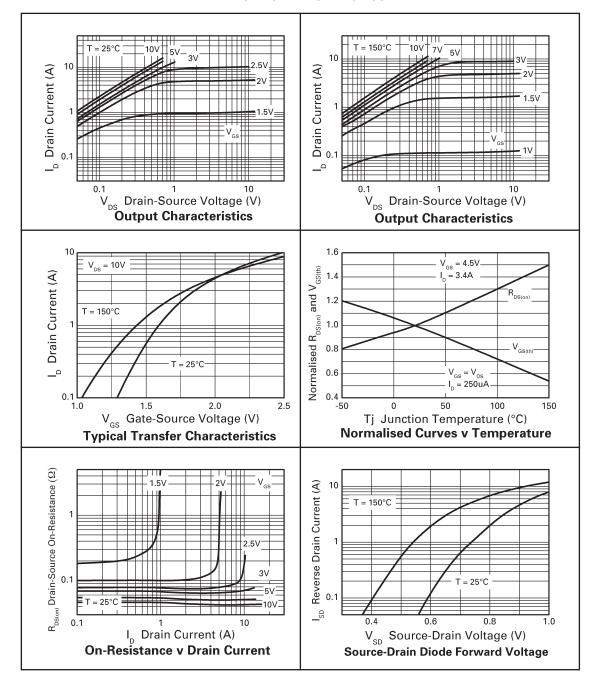
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC	'	1				
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	20			V	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1	μΑ	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V
Gate-Body Leakage	I <sub>GSS</sub>			100	nA	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	0.7			V	I <sub>D</sub> =250μA, V <sub>DS</sub> = V <sub>GS</sub>
Static Drain-Source On-State	R <sub>DS(on)</sub>			0.060	Ω	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.4A
Resistance <sup>(1)</sup>				0.110	Ω	V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.5A
Forward Transconductance (1) (3)	9 <sub>fs</sub>		9.4		S	V <sub>DS</sub> =10V,I <sub>D</sub> =3.4A
DYNAMIC (3)						•
Input Capacitance	C <sub>iss</sub>		544		pF	
Output Capacitance	Coss		132		pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> =0V,
Reverse Transfer Capacitance	C <sub>rss</sub>		85		pF	f=1MHz
SWITCHING <sup>(2) (3)</sup>					•	
Turn-On Delay Time	t <sub>d(on)</sub>		4.0		ns	
Rise Time	t <sub>r</sub>		5.3		ns	$V_{DD} = 10V, V_{GS} = 4.5V$
Turn-Off Delay Time	t <sub>d(off)</sub>		16.6		ns	I <sub>D</sub> = 1A
Fall Time	t <sub>f</sub>		9.5		ns	$R_G \cong 6.0\Omega$
Total Gate Charge	Qg		6.6		nC	
Gate-Source Charge	Q <sub>gs</sub>		1.2		nC	$V_{DS} = 10V, V_{GS} = 4.5V,$
Gate-Drain Charge	Q <sub>gd</sub>		2.1		nC	I <sub>D</sub> =3.4A
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V <sub>SD</sub>		0.85	0.95	V	$T_J = 25^{\circ}C, I_S = (3.3)A,$
						V <sub>GS</sub> =0V
Reverse Recovery Time (3)	t <sub>rr</sub>		11.4		ns	T <sub>J</sub> =25°C, I <sub>F</sub> =(1.7)A,
Reverse Recovery Charge (3)	Q <sub>rr</sub>		4.6		nC	di/dt= 100A/μs

#### **NOTES**

- (1) Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq\!2\%.$
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.



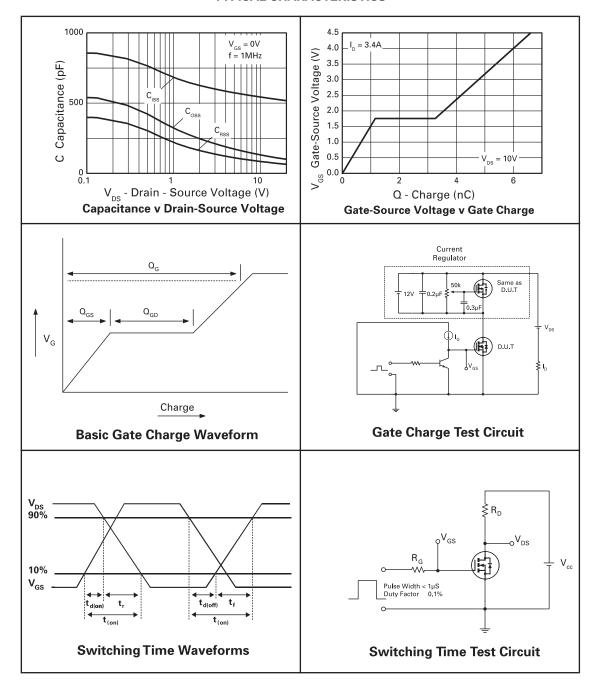
#### **TYPICAL CHARACTERISTICS**







#### **TYPICAL CHARACTERISTICS**





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- "Not recommended for new designs"Device is still in production to support existing designs and production
- "Obsolete"Production has been discontinued

Datasheet status key:

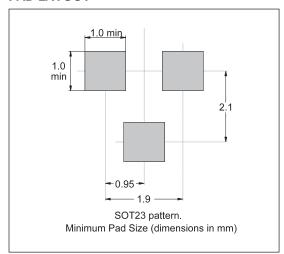
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## **PACKAGE OUTLINE**

# 3 I EAOS D

## **PAD LAYOUT**



Controlling dimensions are in millimetres. Approximate conversions are given in inches

## **PACKAGE DIMENSIONS**

	MILLIMETRES		INCHES			MILLIMETRES		INCHES	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX
Α	2.67	3.05	0.105	0.120	Н	0.33	0.51	0.013	0.020
В	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
С	_	1.10	_	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075	NOM	θ	10° TYP 10°		TYP	

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